Robin John Nicholas

List of Publications by Year
in descending order

319	15,431	29994 54	20900 115
papers	citations	h-index	g-index

320	320	320	14546
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Improving performance of fully scalable, flexible transparent conductive films made from carbon nanotubes and ethylene-vinyl acetate. Energy Reports, 2022, 8, 48-60.	2.5	2
2	Chemical Interaction at the MoO₃/CH₃NH₃PbI_{3â€“x}Cl_x Interface. ACS Applied Materials & Interfaces, 2021, 13, 17085-17092.	4.0	13
3	Filamentary High-Resolution Electrical Probes for Nanoengineering. Nano Letters, 2020, 20, 1067-1073.	4.5	2
4	Giant Fine Structure Splitting of the Bright Exciton in a Bulk MAPbBr₃ Single Crystal. Nano Letters, 2019, 19, 7054-7061.	4.5	41
5	Solubilization of Carbon Nanotubes with Ethylene-Vinyl Acetate for Solution-Processed Conductive Films and Charge Extraction Layers in Perovskite Solar Cells. ACS Applied Materials & Interfaces, 2019, 11, 1185-1191.	4.0	31
6	Structural and Optical Properties of Cs₂AgBiBr₆ Double Perovskite. ACS Energy Letters, 2019, 4, 299-305.	8.8	146
7	Highly Crystalline Methylammonium Lead Tribromide Perovskite Films for Efficient Photovoltaic Devices. ACS Energy Letters, 2018, 3, 1233-1240.	8.8	54
8	Multi-band magnetotransport in exfoliated thin films of Cu_xBi₂Se₃. Journal of Physics Condensed Matter, 2018, 30, 155302.	0.7	3
9	Carbon Nanotubes for Quantum Dot Photovoltaics with Enhanced Light Management and Charge Transport. ACS Photonics, 2018, 5, 4854-4863.	3.2	4
10	Two-Dimensional Excitonic Photoluminescence in Graphene on a Cu Surface. ACS Nano, 2017, 11, 3207-3212.	7.3	11
11	Dopant-Free Planar nâ€“iâ€“p Perovskite Solar Cells with Steady-State Efficiencies Exceeding 18%. ACS Energy Letters, 2017, 2, 622-628.	8.8	73
12	Spatially resolved studies of the phases and morphology of methylammonium and formamidinium lead tri-halide perovskites. Nanoscale, 2017, 9, 3222-3230.	2.8	44
13	Unraveling the Exciton Binding Energy and the Dielectric Constant in Single-Crystal Methylammonium Lead Triiodide Perovskite. Journal of Physical Chemistry Letters, 2017, 8, 1851-1855.	2.1	152
14	Impact of microstructure on the electronâ€“hole interaction in lead halide perovskites. Energy and Environmental Science, 2017, 10, 1358-1366.	15.6	36
15	Carbon Nanotubes in Perovskite Solar Cells. Advanced Energy Materials, 2017, 7, 1601839.	10.2	107
16	Investigating the Role of 4â€Tert Butylpyridine in Perovskite Solar Cells. Advanced Energy Materials, 2017, 7, 1601079.	10.2	106
17	A low viscosity, low boiling point, clean solvent system for the rapid crystallisation of highly specular perovskite films. Energy and Environmental Science, 2017, 10, 145-152.	15.6	319
18	Independence of optical absorption on Auger ionization in single-walled carbon nanotubes revealed by ultrafast eâ€“h photodoping. New Journal of Physics, 2016, 18, 023051.	1.2	0

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19	Research Update: Strategies for improving the stability of perovskite solar cells. APL Materials, 2016, 4, .	2.2	126
20	Quantum dot-like excitonic behavior in individual single walled-carbon nanotubes. Scientific Reports, 2016, 6, 37167.	1.6	6
21	Efficient perovskite solar cells by metal ion doping. Energy and Environmental Science, 2016, 9, 2892-2901.	15.6	372
22	The Impact of Phase Retention on the Structural and Optoelectronic Properties of Metal Halide Perovskites. Advanced Materials, 2016, 28, 10757-10763.	11.1	65
23	Structured Organicâ€“Inorganic Perovskite toward a Distributed Feedback Laser. Advanced Materials, 2016, 28, 923-929.	11.1	257
24	Determination of the exciton binding energy and effective masses for methylammonium and formamidinium lead tri-halide perovskite semiconductors. Energy and Environmental Science, 2016, 9, 962-970.	15.6	603
25	Surface-Effect-Induced Optical Bandgap Shrinkage in GaN Nanotubes. Nano Letters, 2015, 15, 4472-4476.	4.5	21
26	Thiophene-based dyes for probing membranes. Organic and Biomolecular Chemistry, 2015, 13, 3792-3802.	1.5	41
27	Hot carrier relaxation of Dirac fermions in bilayer epitaxial graphene. Journal of Physics Condensed Matter, 2015, 27, 164202.	0.7	19
28	Rapid epitaxy-free graphene synthesis on silicidated polycrystalline platinum. Nature Communications, 2015, 6, 7536.	5.8	46
29	Direct measurement of the exciton binding energy and effective masses for charge carriers in organicâ€“inorganic tri-halide perovskites. Nature Physics, 2015, 11, 582-587.	6.5	1,651
30	Reduced Stark shift in three-dimensionally confined GaN/AlGaN asymmetric multi-quantum disks. Optical Materials Express, 2015, 5, 849.	1.6	3
31	An ultrafast carbon nanotube terahertz polarisation modulator. Journal of Applied Physics, 2014, 115, .	1.1	36
32	Engineering Nanostructures by Binding Single Molecules to Single-Walled Carbon Nanotubes. ACS Nano, 2014, 8, 12748-12754.	7.3	10
33	Low-Temperature Processed Electron Collection Layers of Graphene/TiO₂ Nanocomposites in Thin Film Perovskite Solar Cells. Nano Letters, 2014, 14, 724-730.	4.5	999
34	Enhanced Hole Extraction in Perovskite Solar Cells Through Carbon Nanotubes. Journal of Physical Chemistry Letters, 2014, 5, 4207-4212.	2.1	156
35	Carbon Nanotube/Polymer Composites as a Highly Stable Hole Collection Layer in Perovskite Solar Cells. Nano Letters, 2014, 14, 5561-5568.	4.5	1,073
36	Hyperspectral Imaging of Exciton Photoluminescence in Individual Carbon Nanotubes Controlled by High Magnetic Fields. Nano Letters, 2014, 14, 5194-5200.	4.5	15

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37	Beyond 100 Tesla: Scientific experiments using single-turn coils. Comptes Rendus Physique, 2013, 14, 115-120.	0.3	6
38	Production of Highâ€Purity Singleâ€Chirality Carbon Nanotube Hybrids by Selective Polymer Exchange. Small, 2013, 9, 2245-2249.	5.2	24
39	Novel Carbon Nanotubeâ€Conjugated Polymer Nanohybrids Produced By Multiple Polymer Processing. Advanced Materials, 2013, 25, 4365-4371.	11.1	34
40	Extreme sensitivity of graphene photoconductivity to environmental gases. Nature Communications, 2012, 3, 1228.	5.8	120
41	Environment induced variation in the photoconductivity of graphene observed by terahertz spectroscopy. , 2012, , .		0
42	Nanoengineering Coaxial Carbon Nanotubeâ€“Dual-Polymer Heterostructures. ACS Nano, 2012, 6, 6058-6066.	7.3	36
43	Ultrafast Charge Separation at a Polymerâ^'Single-Walled Carbon Nanotube Molecular Junction. Nano Letters, 2011, 11, 66-72.	4.5	81
44	Electronic and Mechanical Modification of Single-Walled Carbon Nanotubes by Binding to Porphyrin Oligomers. ACS Nano, 2011, 5, 2307-2315.	7.3	50
45	Noncovalent Binding of Carbon Nanotubes by Porphyrin Oligomers. Angewandte Chemie - International Edition, 2011, 50, 2313-2316.	7.2	90
46	Ultrafast Charge Separation at a Single-walled Carbon Nanotube â€“ Polymer Interface. Materials Research Society Symposia Proceedings, 2011, 1286, 7.	0.1	0
47	UVâ€“vis absorption spectroscopy of carbon nanotubes: Relationship between the ï€-electron plasmon and nanotube diameter. Chemical Physics Letters, 2010, 493, 19-23.	1.2	155
48	BAND STRUCTURE AND ELECTRON VELOCITY MEASUREMENT IN CARBON NANOTUBES AND GRAPHENE. International Journal of Modern Physics B, 2009, 23, 2655-2664.	1.0	3
49	Terahertz Excitonic Response of Isolated Single-Walled Carbon Nanotubes. Journal of Physical Chemistry C, 2009, 113, 18106-18109.	1.5	36
50	Observation of a Type II Heterojunction in a Highly Ordered Polymerâ^'Carbon Nanotube Nanohybrid Structure. Nano Letters, 2009, 9, 3871-3876.	4.5	77
51	Investigation of InGaAsP-based solar cells for double-junction photovoltaic devices. Thin Solid Films, 2008, 516, 6744-6747.	0.8	7
52	Polymer Structure and Solvent Effects on the Selective Dispersion of Single-Walled Carbon Nanotubes. Journal of the American Chemical Society, 2008, 130, 3543-3553.	6.6	287
53	Cyclotron resonance of electrons and holes in graphene monolayers. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2008, 366, 237-243.	1.6	14
54	Introduction. Carbon-based electronics: fundamentals and device applications. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2008, 366, 189-193.	1.6	25

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55	Direct spectroscopic evidence of energy transfer from photo-excited semiconducting polymers to single-walled carbon nanotubes. Nanotechnology, 2008, 19, 095603.	1.3	56
56	Temperature-dependent cyclotron resonance in a hybridized electronâ€“hole system in InAs/GaSb heterostructures. Semiconductor Science and Technology, 2007, 22, 194-202.	1.0	7
57	High Magnetic Field Phenomena in Carbon Nanotubes. Topics in Applied Physics, 2007, , 393-422.	0.4	11
58	Implementation and study of photovoltaic cells based on InP lattice-matched InGaAs and InGaAsP. , 2007, , .		0
59	Highly selective dispersion of single-walled carbon nanotubes using aromatic polymers. Nature Nanotechnology, 2007, 2, 640-646.	15.6	988
60	Temperature induced restoration of fluorescence from oxidised single-walled carbon nanotubes in aqueous sodium dodecylsulfate solution. Physical Chemistry Chemical Physics, 2006, 8, 3547.	1.3	37
61	The effects of nitrogen and boron doping on the optical emission and diameters of single-walled carbon nanotubes. Carbon, 2006, 44, 2752-2757.	5.4	53
62	Current-driven breakdown of the quantized Hall states of a broken-gap 2D electronâ€“hole system. Semiconductor Science and Technology, 2006, 21, 1758-1763.	1.0	1
63	Magnetic separation of Fe catalyst from single-walled carbon nanotubes in an aqueous surfactant solution. Carbon, 2005, 43, 1151-1155.	5.4	27
64	Diameter-selective encapsulation of metallocenes in single-walled carbon nanotubes. Nature Materials, 2005, 4, 481-485.	13.3	245
65	Chirality-dependent boron-mediated growth of nitrogen-doped single-walled carbon nanotubes. Physical Review B, 2005, 72, .	1.1	33
66	Comparative study of photoluminescence of single-walled carbon nanotubes wrapped with sodium dodecyl sulfate, surfactin and polyvinylpyrrolidone. Nanotechnology, 2005, 16, S202-S205.	1.3	49
67	Bandgap-selective chemical doping of semiconducting single-walled carbon nanotubes. Nanotechnology, 2004, 15, 1844-1847.	1.3	15
68	Chirality Assignment of Single-Walled Carbon Nanotubes with Strain. Physical Review Letters, 2004, 93, 156104.	2.9	59
69	Mid-infrared electroluminescence from coupled quantum dots and wells. Journal of Applied Physics, 2004, 96, 2725-2730.	1.1	0
70	Controlled orientation of ellipsoidal fullerene C70 in carbon nanotubes. Applied Physics Letters, 2004, 84, 792-794.	1.5	63
71	MAGNETO-PHOTOLUMINESCENCE OF CHIRALITY-CHARACTERIZED SINGLE-WALLED CARBON NANOTUBES. International Journal of Modern Physics B, 2004, 18, 3509-3512.	1.0	10
72	Properties of narrow gap quantum dots and wells in the InAs/InSb/GaSb systems. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 20, 204-210.	1.3	13

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73	Mid-infrared luminescence from coupled quantum dots and wells. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 341-344.	1.3	3
74	Magnetoresistance studies of strongly coupled superlattices. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 316-319.	1.3	1
75	Far infrared modulated photoluminescence in InSb quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 598-602.	1.3	1
76	Comparative studies on acid and thermal based selective purification of HiPCO produced single-walled carbon nanotubes. Chemical Physics Letters, 2004, 386, 239-243.	1.2	95
77	Quantum Hall and insulating states of a 2-D electronâ€“hole system. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 20, 160-171.	1.3	4
78	Magneto-photoluminescence studies of a novel quantum dotâ€“quantum well coupled system. Physica Status Solidi (B): Basic Research, 2003, 238, 281-284.	0.7	3
79	Magnetic-field-induced suppression of tunnelling into a two-dimensional electron system. Journal of Physics Condensed Matter, 2002, 14, 5561-5574.	0.7	3
80	Spin polarization of 2D electrons in the quantum Hall ferromagnet: evidence for a partially polarized state around filling factor one. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 12-15.	1.3	4
81	Mass enhancement and electronâ€“hole coupling in InAs/GaSb bilayers studied by cyclotron resonance. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 289-292.	1.3	9
82	The quantum Hall effect in an InAs/GaSb based electronâ€“hole system and its current-driven breakdown. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 161-164.	1.3	1
83	Anomalous g-factors and diamagnetic shifts of biexcitons in ZnS quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 507-511.	1.3	1
84	Tunable mid-IR emission using a novel quantum dotâ€“quantum well coupled system. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 241-245.	1.3	5
85	Magnetoresistance of vertical transport in InAs/GaSb superlattices. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 736-740.	1.3	0
86	Atomic Self-ordering in Heteroepitaxially Grown Semiconductor Quantum Dots due to Relaxation of External Lattice Mismatch Strains. Materials Research Society Symposia Proceedings, 2001, 696, 1.	0.1	1
87	Atomic Self-Ordering in Heteroepitaxially Grown Semiconductor Quantum Dots Due to Relaxation of External Lattice Mismatch Strains. Materials Research Society Symposia Proceedings, 2001, 707, 881.	0.1	1
88	InGaAs/GaAs quantum wells and quantum dots on (111)B orientation. Solid State Communications, 2001, 117, 649-654.	0.9	3
89	Breakdown of the quantum Hall effect in an electronâ€“hole system. Physica B: Condensed Matter, 2001, 298, 8-12.	1.3	8
90	Edge effects in an insulating state of an electronâ€“hole system in magnetic field. Physica B: Condensed Matter, 2001, 298, 28-32.	1.3	2

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91	The effect of the cross-gap alignment on magneto-transport in short period InAs/GaSb superlattices. Physica B: Condensed Matter, 2001, 298, 344-347.	1.3	1
92	MOVPE grown self-assembled and self-ordered InSb quantum dots in a GaSb matrix assessed by AFM, CTEM, HRTEM and PL. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 112-115.	1.7	24
93	Magneto-photoluminescence of AlGaN/GaN quantum wells. Journal of Crystal Growth, 2001, 230, 487-491.	0.7	4
94	Excitons with large binding energies in MgS/ZnSe/MgS and ZnMgS/ZnS/ZnMgS quantum wells. Journal of Physics Condensed Matter, 2001, 13, 2317-2329.	0.7	11
95	Internal self-ordering in In(Sb,As), (In,Ga)Sb, and (Cd,Zn,Mn)Se nano-agglomerates/quantum dots. Applied Physics Letters, 2001, 79, 946-948.	1.5	16
96	Infrared single wavelength gas composition monitoring for metalorganic vapour-phase epitaxy. Journal of Crystal Growth, 2000, 221, 166-171.	0.7	18
97	Cyclotron resonance in an asymmetric electronâ€“hole InAs/GaSb DHET structure. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 660-663.	1.3	3
98	A digital quantum Hall effect. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 836-839.	1.3	1
99	Designs for a quantum cascade laser using interband carrier extraction. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 84-88.	1.3	7
100	Intersubband transitions in InAs/GaSb superlattices in a parallel magnetic field. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 93-96.	1.3	3
101	MOVPE grown self-assembled Sb-based quantum dots assessed by means of AFM and TEM. IEE Proceedings: Optoelectronics, 2000, 147, 209-215.	0.8	13
102	The upgrade of the Oxford High Magnetic Field Laboratory. IEEE Transactions on Applied Superconductivity, 2000, 10, 1552-1555.	1.1	6
103	Metal-Insulator Oscillations in a Two-Dimensional Electron-Hole System. Physical Review Letters, 2000, 85, 2364-2367.	2.9	26
104	A far infrared modulated photoluminescence (FIRM-PL) study of cyclotron resonance in a 2D electron gas in GaAs/AlxGa1-xAs heterojunctions. Semiconductor Science and Technology, 1999, 14, 768-774.	1.0	9
105	Searches for skyrmions in the limit of zero -factor. Semiconductor Science and Technology, 1998, 13, 671-679.	1.0	20
106	Skyrmions and composite fermions in the limit of vanishing Zeeman energy. Journal of Physics Condensed Matter, 1998, 10, 11327-11335.	0.7	3
107	Improved photoluminescence from electrochemically passivated GaSb. Semiconductor Science and Technology, 1997, 12, 413-418.	1.0	18
108	Optical studies of localized excitons in symmetric coupled quantum wells. Superlattices and Microstructures, 1997, 21, 597-600.	1.4	2

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109	Selective area epitaxy of InGaAs/InGaAsP quantum wells studied by magnetotransport. Semiconductor Science and Technology, 1996, 11, 735-740.	1.0	4
110	Magneto-optical studies of the type I/type II crossover and band offset in superlattices in magnetic fields up to 45 T. Solid-State Electronics, 1996, 40, 69-74.	0.8	1
111	Interface and layer thickness dependence of the effective mass in superlattices studied by high field cyclotron resonance. Solid-State Electronics, 1996, 40, 181-184.	0.8	13
112	Magneto-optical studies of compressively strained multiple quantum wells. Solid-State Electronics, 1996, 40, 597-600.	0.8	4
113	Photoconductivity studies of InAsP/InP heterostructures in applied magnetic and electric fields. Semiconductor Science and Technology, 1996, 11, 34-38.	1.0	3
114	Growth of strained layer superlattices. II. Journal of Crystal Growth, 1995, 146, 495-502.	0.7	27
115	Magneto-optical studies of the type-I/type-II crossover and band offset in ZnTe/Zn1â^'xMnxTe superlattices in magnetic fields up to 45 T. Physical Review B, 1995, 52, 5269-5274.	1.1	12
116	Magnetotransport in a pseudomorphic GaAs/Ga0.8In0.2As/Ga0.75Al0.25As heterostructure with a Si Î´-doping layer. Physical Review B, 1995, 52, 12218-12231.	1.1	52
117	Influence of light on the confinement potential of GaAs/AlxGa1â^'xAs heterojunctions. Physical Review B, 1995, 52, 2688-2696.	1.1	26
118	Cyclotron-resonance measurements onp-type strained-layerSi1â^'xGex/Si heterostructures. Physical Review B, 1995, 51, 13499-13502.	1.1	11
119	Resonant cavity-enhanced (RCE) photodetector based on Ga(In)Sb for gas-sensing applications. Semiconductor Science and Technology, 1995, 10, 1017-1021.	1.0	8
120	A modified phenomenological description of the exchange interactions in dilute magnetic semiconductors. Semiconductor Science and Technology, 1995, 10, 791-796.	1.0	14
121	Temperature dependence of the band overlap in InAs/GaSb structures. Physical Review B, 1995, 51, 1729-1734.	1.1	15
122	An optically detected cyclotron resonance study of bulk GaAs. Semiconductor Science and Technology, 1994, 9, 198-206.	1.0	24
123	Electroluminescence out to 2.1 mu m observed in GaSb/InxGa1-xSb quantum wells grown by MOVPE. Semiconductor Science and Technology, 1994, 9, 87-90.	1.0	17
124	Collapse of High Field Magnetophonon Resonance in GaAs-GaAlAs Heterojunctions. Physical Review Letters, 1994, 73, 589-592.	2.9	23
125	Interband magneto-optical studies of resonant polaron coupling in CdTe/Cd1â^'xMnxTe quantum wells. Physical Review B, 1994, 50, 7596-7601.	1.1	10
126	[001]- and piezoelectric-[111]-oriented InAs/GaSb structures under hydrostatic pressure. Physical Review B, 1994, 49, 16614-16621.	1.1	22

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127	Measurements of the effective mass and scattering times of composite fermions from magnetotransport analysis. Physical Review Letters, 1994, 72, 1906-1909.	2.9	169
128	Magneto-optical study ofGa1â^'xInxSb/GaSb strained-quantum-well structures: Miniband formation and valence-band structure. Physical Review B, 1994, 49, 11210-11221.	1.1	8
129	Observation of magnetic-field-induced semimetal-semiconductor transitions in crossed-gap superlattices by cyclotron resonance. Physical Review B, 1994, 49, 10474-10483.	1.1	23
130	One dimensional transport and gating of InAs/GaSb structures. Superlattices and Microstructures, 1994, 15, 41.	1.4	6
131	Optical and magnetotransport properties of semimetallic InAs/(In,Ga)Sb superlattices. Physica B: Condensed Matter, 1994, 201, 271-279.	1.3	18
132	Pulsed and high temperature superconducting magnet technology in Oxford. Physica B: Condensed Matter, 1994, 201, 546-550.	1.3	9
133	Direct observation of the semimetal to semiconductor transition in crossed band gap superlattices at magnetic fields of up to 150 T. Solid-State Electronics, 1994, 37, 1027-1030.	0.8	2
134	Cyclotron and intersubband resonance studies in [001] and piezoelectric [111] InAs/(Ga,In)Sb superlattices. Solid-State Electronics, 1994, 37, 1227-1230.	0.8	6
135	Growth of InAs/GaSb strained layer superlattices. I. Journal of Crystal Growth, 1994, 145, 778-785.	0.7	39
136	Variations of the hole effective masses induced by tensile strain inIn1â^'xGaxAs(P)/InGaAsP heterostructures. Physical Review B, 1994, 50, 7660-7667.	1.1	8
137	Orientation and pressure dependence of the band overlap in InAs/GaSb structures. Semiconductor Science and Technology, 1994, 9, 118-122.	1.0	18
138	Effective mass and quantum lifetime in a Si/Si0.87Ge0.13/Si twoâ€dimensional hole gas. Applied Physics Letters, 1994, 64, 357-359.	1.5	37
139	Cyclotron resonance to 100 mK of a GaAs heterojunction in the ultra-quantum limit. Surface Science, 1994, 305, 33-41.	0.8	11
140	â€œIntrinsicâ€•quantum Hall effect in InAs/Ga1â^'xInxSb crossed gap heterostructures in high magnetic fields. Surface Science, 1994, 305, 156-160.	0.8	14
141	Disappearance of magnetophonon resonance at high magnetic fields in GaAs/GaAlAs heterojunctions. Surface Science, 1994, 305, 327-332.	0.8	1
142	Magneto-optical properties of Mn-based IIâ€“VI semimagnetic superlattices. Physica B: Condensed Matter, 1993, 191, 156-170.	1.3	6
143	A magneto-optical study of coupled quantum wells in strained GaInSb/GaSb. Physica B: Condensed Matter, 1993, 184, 106-110.	1.3	14
144	Cyclotron resonance measurements of the hole mass in [0 0 1] and [1 1 1] InxGa1â^'xSb/GaSb quantum wells. Physica B: Condensed Matter, 1993, 184, 154-158.	1.3	3

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145	Optically detected cyclotron resonance of GaAs quantum wells. Physica B: Condensed Matter, 1993, 184, 159-163.	1.3	10
146	Ultra-high magnetic field cyclotron resonance of zero-gap InAs/GaSb superlattices. Physica B: Condensed Matter, 1993, 184, 168-172.	1.3	8
147	High-field magneto-resistance in GaAs-GaAlAs heterojunctions. Physica B: Condensed Matter, 1993, 184, 197-201.	1.3	3
148	Magnetotransport studies of GaSb/InAs crossed gap heterostructures in high magnetic fields. Physica B: Condensed Matter, 1993, 184, 202-205.	1.3	1
149	High magnetic field studies of the crossed-gap superlattice system InAs/GaSb. Physica B: Condensed Matter, 1993, 184, 268-276.	1.3	20
150	Magnetic-field- and temperature-dependent exciton delocalisation in a CdTe/Cd1â^'xMnxTe superlattice. Physica B: Condensed Matter, 1993, 184, 455-459.	1.3	2
151	The design of quantum-confined Stark effect modulators for integration with 1.5 mu m lasers. Semiconductor Science and Technology, 1993, 8, 1173-1178.	1.0	11
152	Magnetotransport investigations at InSb and Hg1-xCdxTe bicrystals in tilted magnetic fields. Semiconductor Science and Technology, 1993, 8, S168-S171.	1.0	4
153	Devices and desires in the 2-4 mu m region based on antimony-containing III-V heterostructures grown by MOVPE. Semiconductor Science and Technology, 1993, 8, S380-S385.	1.0	22
154	The control and evaluation of blue shift in GaInAs/GaInAsP multiple quantum well structures for integrated lasers and Stark-effect modulators. Semiconductor Science and Technology, 1993, 8, 1156-1165.	1.0	5
155	Cyclotron resonance of high-mobility GaAs/AlGaAs (311) 2DHGs. Semiconductor Science and Technology, 1993, 8, 1465-1469.	1.0	20
156	Unusual behaviour of the Ge DX centre in GaAs: coexistence of two localized donor states. Journal of Physics Condensed Matter, 1993, 5, 5001-5008.	0.7	5
157	High-field magnetoresistance in GaAs/Ga0.7Al0.3As heterojunctions arising from elastic and inelastic scattering. Physical Review B, 1993, 48, 5457-5468.	1.1	21
158	Magnetoconductivity in a mesoscopic antidot array. Physical Review B, 1993, 47, 7348-7353.	1.1	18
159	Optical and transport properties of piezoelectric [111]-oriented strainedGa1â^'xInxSb/GaSb quantum wells. Physical Review B, 1993, 48, 17885-17891.	1.1	6
160	Low-field magnetotransport study of localization in a mesoscopic antidot array. Physical Review B, 1993, 47, 7354-7360.	1.1	8
161	Superlattice modification of the valence-band spin splitting inInxGa1â^'xAs/GaAs superlattices up to 45 T. Physical Review B, 1993, 48, 12323-12325.	1.1	8
162	New phases of the 2D electron system in the ultra-quantum limit observed by cyclotron resonances. Physical Review Letters, 1993, 70, 2150-2153.	2.9	48

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163	Piezoelectric effects in superlattices. Semiconductor Science and Technology, 1993, 8, S367-S372.	1.0	15
164	Unusual Behaviour of the DX-Centre in GaAs:Ge. Japanese Journal of Applied Physics, 1993, 32, 218.	0.8	7
165	Spin Split Cyclotron Resonance in a 2-D Electron System at Very High Magnetic Fields. Journal of the Physical Society of Japan, 1993, 62, 1267-1271.	0.7	11
166	Superlattice dispersion in InGaAs/InGaAsP multi-quantum wells. Semiconductor Science and Technology, 1992, 7, 493-497.	1.0	8
167	Cyclotron resonance of the quasi-two-dimensional electron gas at Hg1-xCdxTe grain boundaries. Semiconductor Science and Technology, 1992, 7, 511-515.	1.0	3
168	Magnetotransport investigations and modelling of the Hg1-xCdxTe-anodic oxide accumulation system. Semiconductor Science and Technology, 1992, 7, 810-817.	1.0	9
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